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November 2007

# FDC365P

# P-Channel PowerTrench<sup>®</sup> MOSFET -35V, -4.3A, $55m\Omega$

#### **Features**

- Max  $r_{DS(on)} = 55m\Omega$  at  $V_{GS} = -10V$ ,  $I_D = -4.2A$
- Max  $r_{DS(on)} = 80 m\Omega$  at  $V_{GS} = -4.5 V$ ,  $I_D = -3.2 A$
- RoHS Compliant

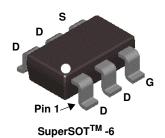
# **General Description**

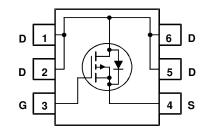
This P-Channel MOSFET has been produced using Fairchild Semiconductor's proprietary PowerTrench technology to deliver low  $r_{DS(on)}$  and optimized Bvdss capability to offer superior performance benefit in the applications.

### **Applications**

- Inverter
- Power Supplies







# MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
$V_{DS}$	Drain to Source Voltage		-35	V	
$V_{GS}$	Gate to Source Voltage		±20	V	
I <sub>D</sub>	-Continuous	(Note 1a)	-4.3		
	-Pulsed		-20	Α	
Б	Power Dissipation	(Note 1a)	1.6	147	
$P_{D}$	Power Dissipation	(Note 1b)	0.8	W	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C	

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	156	C/VV

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.365P	FDC365P	SSOT6	7"	8mm	3000 units

# **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Characteristics							
$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-35			V	
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, referenced to 25°C		-26		mV/°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -28V, V_{GS} = 0V$			-1	μΑ	
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA	

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-1	-1.8	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, referenced to 25°C		5.0		mV/°C
		$V_{GS} = -10V, I_D = -4.2A$		45	55	
r <sub>DS(on)</sub>	` '	$V_{GS} = -4.5V$ , $I_D = -3.2A$		70	80	mΩ
, ,		$V_{GS} = -10V$ , $I_D = -4.2A$ , $T_J = 125$ °C		69	90	
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = -10V, I_{D} = -4.2A$		8.7		S

# **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 00V V 0V		530	705	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = -20V, V_{GS} = 0V,$ f = 1MHz		105	135	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 = 1101112		55	80	pF
$R_g$	Gate Resistance	f = 1MHz		6.1		Ω

# **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time			7	13	ns
t <sub>r</sub>	Rise Time	$V_{DD} = -20V, I_{D} = -4.2A$ $V_{GS} = -10V, R_{GEN} = 6$	λ,	3	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	v <sub>GS</sub> = -10v, n <sub>GEN</sub> = 0	52	15	28	ns
t <sub>f</sub>	Fall Time			3	10	ns
$Q_g$	Total Gate Charge	V <sub>GS</sub> = 0V to -10V	001/	11	15	nC
Qg	Total Gate Charge	$V_{GS} = 0V \text{ to } -5V$	D = -20V,	6	9	nC
Q <sub>gs</sub>	Gate to Source Charge	ID.	= -4.2A	1.7		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			2.2		nC

## **Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = -1.3A$ (Note 2)		-0.8	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	$I_F = -4.2A$ , di/dt = 100A/ $\mu$ s		16	29	ns
Q <sub>rr</sub>	Reverse Recovery Charge			7	14	nC

#### Notes:

In Re<sub>IJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>iJC</sub> is guaranteed by design while R<sub>iJA</sub> is determined by the user's board design.



a.78°C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper on FR-4 board.



b.156°C/W when mounted on a minimum pad of 2 oz copper.

<sup>2:</sup> Pulse Test: Pulse Width <  $300\mu s$ , Duty cycle < 2.0%.

# Typical Characteristics T<sub>JI</sub> = 25°C unless otherwise noted

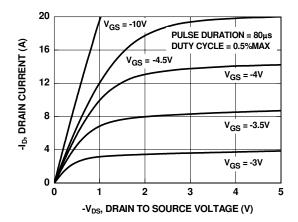


Figure 1. On-Region Characteristics

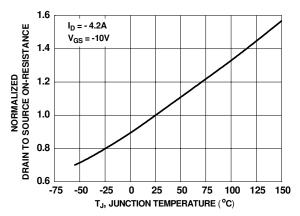


Figure 3. Normalized On-Resistance vs Junction Temperature

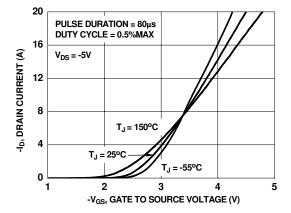


Figure 5. Transfer Characteristics

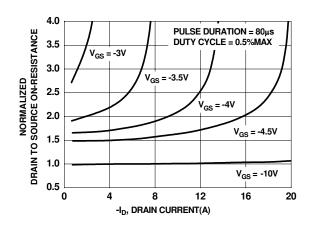


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

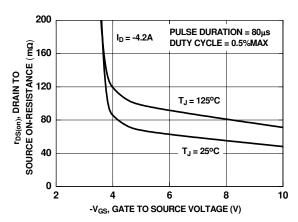


Figure 4. On-Resistance vs Gate to Source Voltage

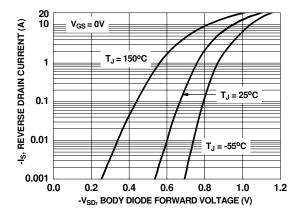


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

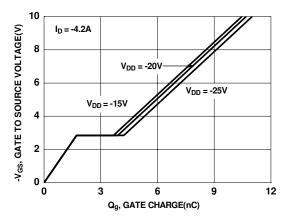


Figure 7. Gate Charge Characteristics

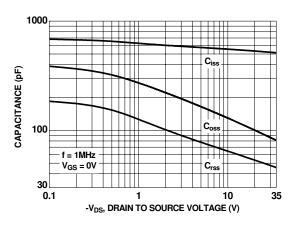


Figure 8. Capacitance vs Drain to Source Voltage

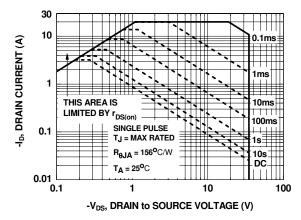


Figure 9. Forward Bias Safe Operating Area

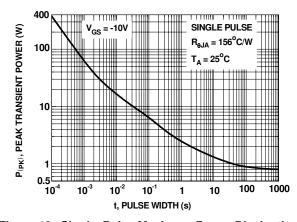


Figure 10. Single Pulse Maximum Power Dissipation

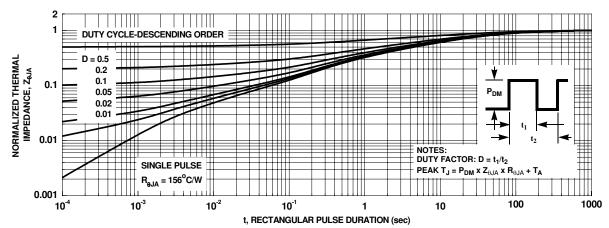
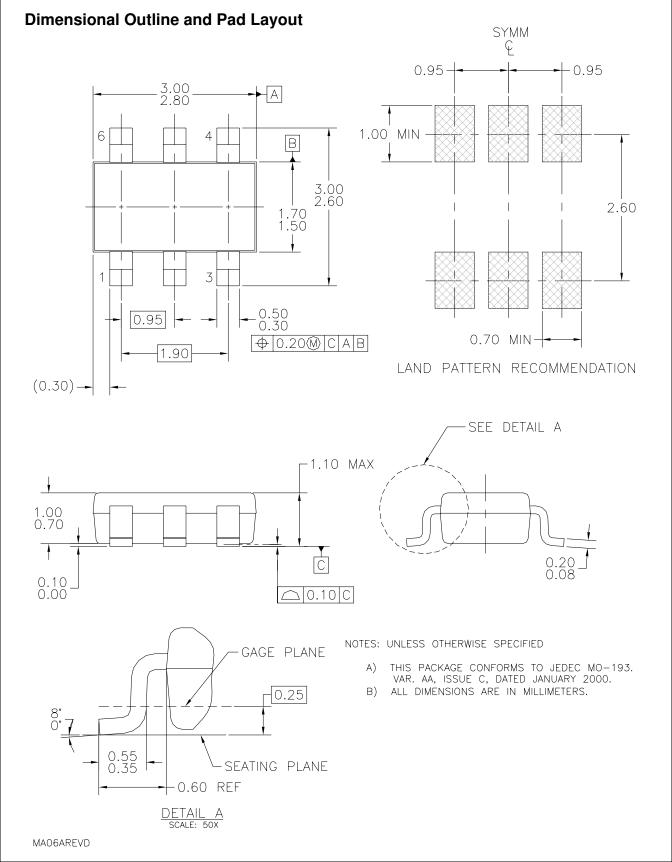


Figure 11. Transient Thermal Response Curve



#### **Preliminary Datasheet**



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